insulating films,

wherein the p-channel TFT of the driver circuit comprises a channel forming region a source region and a drain region in contact with the channel forming region,

wherein the p-channel TFT of the driver circuit does not have a LDD region,

wherein the n-channel TFT of the driver circuit comprises a channel forming region, an n-type impurity region of a first concentration which forms at least one LDD region in contact with the channel forming region and partly overlapping the gate electrode, and a source region and a drain region in contact with the at least one LDD region,

wherein the pixel TFT comprises a channel forming region, at least one LDD region in contact with the channel forming region, and a source region and a drain region in contact with the at least one LDD region.

3. (Amended) A semiconductor device comprising:

a pixel TFT disposed in a pixel section over a first substrate;

a driver circuit comprising a p-channel TFT and an n-channel TFT over the first substrate;

a first interlayer insulating film comprising an inorganic insulating material over a gate electrode of the pixel TFT;

a second interlayer insulating film comprising an organic insulating material over the first interlayer insulating film; and

a pixel electrode having a light reflective surface over the second interlayer insulating film, and electrically connected with the pixel TFT through an opening in the first and second interlayer insulating films,

at least one columnar spacer covering the opening;

a second substrate having a transparent conductive film stuck to the first substrate through

the at least one columnar spacer; and

a liquid crystal sandwiched between the first and second substrates,

wherein the p-channel TFT of the driver circuit comprises a channel forming region a source region and a drain region in contact with the channel forming region,

wherein the p-channel TFT of the driver circuit does not have a LDD region,

Cont'd B2

wherein the n-channel TFT of the driver circuit comprises a channel forming region, an n-type impurity region of a first concentration which forms at least one LDD region in contact with the channel forming region and partly overlapping a gate electrode, and a source region and a drain region in contact with the at least one LDD region,

wherein the pixel TFT comprises a channel forming region, at least one LDD region in contact with the channel forming region, and a source region and a drain region in contact with the at least one LDD region.

21. A semiconductor device according to claim 3 wherein the columnar spacer is formed over the p-channel TFT and the n-channel TFT of the driver circuit.

23. A semiconductor device according to claim 3 wherein the columnar spacer is formed to cover at least a source wiring or a drain wiring of the p-channel TFT and the n-channel TFT of the driver circuit.

25. A semiconductor device according to claim 1 wherein the semiconductor device is in an apparatus selected from a group consisting of a personal computer, a video camera, a portable information terminal, a digital camera, a digital video disc player, an electronic game machine and a projector.

27. A semiconductor device according to claim 3 wherein the semiconductor device is in an apparatus selected from a group consisting of a personal computer, a video camera, a portable information terminal, a digital camera, a digital video disc player, an electronic game machine and a projector.

53. (Amended) A semiconductor device comprising:

a pixel TFT having disposed in a pixel section over a substrate;

a driver circuit comprising a p-channel TFT and an n-channel TFT over the substrate,

a first interlayer insulating film comprising an inorganic insulating material formed over the pixel section;

a second interlayer insulating film comprising an organic insulating material over the first interlayer insulating film;

a pixel electrode having a light reflective surface over the second interlayer insulating film, and in connected to the pixel TFT through an opening formed in the first and second interlayer insulating films;

a source wiring over the second interlayer insulating film;

an alignment film formed over the pixel electrode and the source wiring; and

a liquid crystal interposed between the alignment film and an opposed substrate,

wherein the p-channel TFT of the driver circuit comprises a channel forming region a source region and a drain region in contact with the channel forming region,

wherein the p-channel TFT of the driver circuit does not have a LDD region,

wherein the n-channel TFT of the driver circuit comprises a channel forming region, an n-type impurity region of a first concentration which forms at least one LDD region in contact with the channel forming region and partly overlapping a gate electrode, and a source region and a drain